**Advances in Condensed Matter Physics**

**DC Performance Variations of SOI FinFETs with Different Silicide Thickness**

Jun-Sik Yoon1

1 POSTECH Information Research Laboratories, Pohang 37673, Republic of Korea

Correspondence should be addressed to Jun-Sik Yoon; junsikyoon@postech.ac.kr



Figure S1: On-state resistance (*Ron*) as a function of fin width (*Wfin*) for different *Tsili* of 8 and 10 nm. The number of fins (*Nfin*) for each device is 20. As *Wfin* increases from 40 to 80 nm, the difference of *Ron* between two different *Tsili* decreases from 36 to 23 %.